

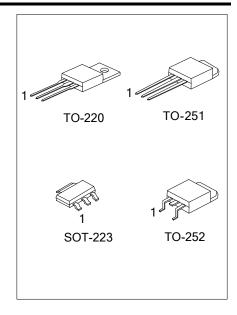
HJ45H11

PNP SILICON TRANSISTOR

PNP EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The HJ45H11 is designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1MHz;series, shunt and switching regulators; low and high frequency inverters/converters; and many others.

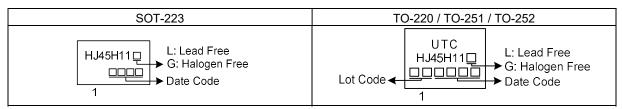


ORDERING INFORMATION

Ordering Number		Deskans	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
HJ45H11L-AA3-R	HJ45H11G-AA3-R	SOT-223	В	С	Е	Tape Reel	
HJ45H11L-TA3-T	HJ45H11G-TA3-T	TO-220	В	С	Е	Tube	
HJ45H11L-TM3-T	HJ45H11G-TM3-T	TO-251	В	С	Е	Tube	
HJ45H11L-TN3-R	HJ45H11G-TN3-R	TO-252	В	С	Е	Tape Reel	
HJ45H11L-TN3-T	HJ45H11G-TN3-T	TO-252	В	С	Е	Tube	
Note: Pin Assignment: B: Bas	e C: Case E: Emitter						

HJ45H11G-AA3-R (1)Packing Type (2)Package Type (3)Green Package	 (1) R: Tape Reel, T: Tube (2) AA3: SOT-223, TA3: TO-220, TM3; TO-251 TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector- Emitter Voltage		V _{CEO}	-80	V
Collector-Emitter Voltage		V _{CES}	-80	V
Emitter-Base Voltage		V _{EBO}	-5	V
Collector Current		lc	-10	A
Base Current		I _B	-5	A
	SOT-223	- P _D	5	W
	TO-220		65	W
Power Dissipation (T _C =25°C)	TO-251 TO-252		20	w
Junction Temperature	tion Temperature		-40 ~ +150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
	SOT-223		25	°C/W
lumetice to Coose (Nets)	TO-220	0	1.92	°C/W
Junction to Case (Note)	TO-251	θ _{JC}	0.05	°0111
	TO-252		6.25	°C/W

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

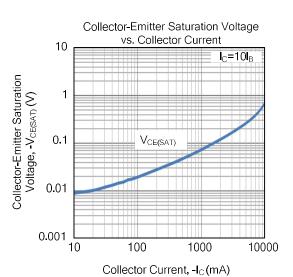
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-30mA, I _B =0	-80			V
Collector-Emitter Breakdown Voltage	BV _{CES}	I _C =-1mA, I _B =0	-80			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =-1mA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-80V, V _{EB} =0			-1	uA
Collector Cut-Off Current	I _{CES}	V _{CE} =-80V, V _{EB} =0			-1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-1	uA
Collector-Emitter Saturation Voltage(Note)	V _{CE(SAT)}	I _C =-8A, I _B =-0.8A			-1	V
Base-Emitter Saturation Voltage(Note)	V _{BE(SAT)}	I _C =-8A, I _B =-0.8A			-1.5	V
	h _{FE1}	V _{CE} =-1V, I _C =-2A	60			
DC Current Gain (Note)	h _{FE2}	V _{CE} =-1V, I _C =-4A	40			
Output Capacitance	Сов	V _{CB} =-10V		120		pF
Transition Frequency	f⊤	V _{CE} =10V, I _C =500mA, f=20MHz		50		MHz
Delay and Rise Times	t _D + t _R	I _C =-5.0A, I _{B1} =-0.5A		33		ns
Storage Time	ts			1720		ns
Fall Time	t _F	I _C =-5.0A, I _{B1} = I _{B2} =-0.5A		150		ns

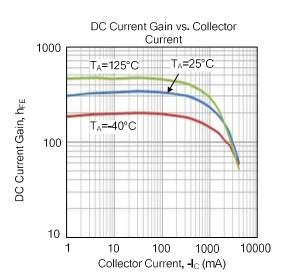
Note: Pulse Test: Pulse Width \leq 380us, Duty Cycle \leq 2%.

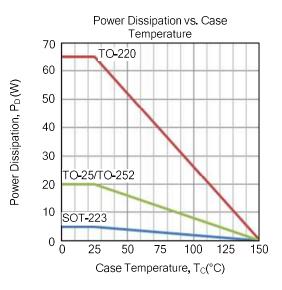


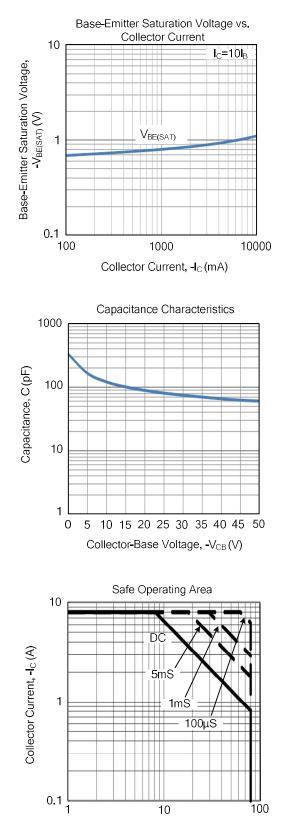
HJ45H11

TYPICAL CHARACTERISTICS









Collector-Emitter Voltage, $-V_{CE}$ (V)



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